

IN THE SPECIFICATION:

Page 2, please amend the paragraph starting in line 1 as follows:

FIGS. 1A to ~~4D~~ 1B are partial sectional views used to describe a conventional method for manufacturing a MOS transistor.

Page 2, please amend the paragraph starting in line 16 as follows:

Subsequently, titanium 8 is deposited to a thickness of approximately 400Å over the entire surface of the silicon wafer 1 by a sputtering method, then RTP (rapid thermal processing) is performed for about 30 seconds and at a temperature of roughly 750 Å while injecting nitrogen at a flow rate of approximately 50 sccm. As a result, with reference to FIG. ~~4B~~ 1A, titanium silicide 8' is formed by the reaction between titanium and silicon. The titanium on the side walls 6 and the field oxidation film 2 is not reacted and therefore remains as unreacted titanium 8.

Page 2, please amend the paragraph starting in line 23 as follows:

The unreacted titanium 8 is a metal and so may interfere with device operation. The unreacted titanium 8 is therefore removed using a solvent. Also, in order to reduce the resistance of the silicide 8' and increase the strength of the same, a heat process is performed in a nitrogen environment and at a temperature of approximately 910 Å.

Page 3, please amend the paragraph starting in line 4 as follows:

After the above processes, in order to form a liner film that is used as an etching completion layer during etching to form contact holes, a silicon nitride film 9, with reference to FIG. ~~4C~~ 1A, is formed to a thickness of roughly 300 Å using plasma enhanced chemical vapor deposition (PECVD).

Page 3, please amend the paragraph starting in line 8 as follows:

In the above process, the silicon nitride film 9 is less thickly deposited at depressed areas adjacent to the device region (one of which is circled using a dotted line in FIG. ~~4C~~ 1A)

than in other areas. The depressed areas are formed as a result of structural problems occurring when forming the field oxidation film 2.

Page 3, please amend the paragraph starting in line 17 as follows:

Subsequently, to prepare for the formation of contact holes, a photosensitive film pattern 11 is formed on the flattened PMD layer 10. With reference to FIG. ~~4D~~ 1B, exposed areas of the PMD layer 10 are then etched using the photosensitive film pattern 11 as a mask to thereby form contact holes 12.

Page 3, please amend the paragraph starting in line 24 as follows:

In the above conventional method for manufacturing a MOS transistor, the silicon nitride film 9, which is used as an etching completion layer, is not formed to a uniform thickness. As a result, when etching the PMD layer 10, the areas of the silicon nitride film 9 formed over the depressed areas of the field oxidation film 2 adjacent to the device region are more quickly etched than other areas of the silicon nitride film 9. Therefore, a contact spiking phenomenon occurs, in which the silicon nitride film 9 is over-etched past where the field oxidation film 2 (under these areas of the silicon nitride film 9) starts. One such area is circled using a dotted line in FIG. ~~4D~~ 1B. The contact spiking phenomenon ultimately results in the interference of the flow of current in the source 7 and the drain 7 such that the semiconductor device operates improperly.

Page 5, please amend the paragraph starting in line 21 as follows:

FIGS. 1A to ~~4D~~ 1B are partial sectional views used to describe a conventional method for manufacturing a MOS transistor.